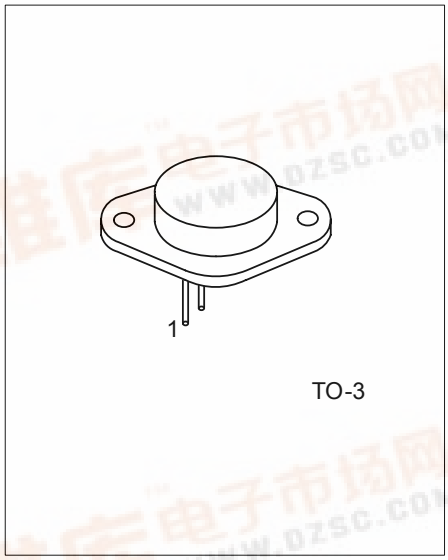
2N2955

PNP SILICON TRANSISTOR

SILICON PNP TRANSISTORS



*Pb-free plating product number:2N2955L

■ DESCRIPTION

The UTC 2N2955 is a silicon PNP transistor in TO-3 metal case. It is intended for power switching circuits, series and shunt regulators, output stages and high fidelity amplifiers.

■ ORDERING INFORMATION

Order Number		Package	Pin Assignment			Packing
Normal	Lead Free Plating		1	2	3	
2N2955-T30-K	2N2955L-T30-K	TO-3	E	B	C	Bulk

Note: 3: Case

2N2955L-T30-K

(1)Packing Type — (1) K: Bulk

(2)Package Type — (2) T30: TO-3

(3)Lead Plating — (3) L: Lead Free Plating, Blank: Pb/Sn

■ ABSOLUTE MAXIMUM RATINGS (Ta=25°C ,unless otherwise specified)

PARAMETERS	SYMBOL	RATINGS	UNITS
Collector-Base Voltage	V_{CBO}	100	V
Collector-Emitter Voltage	V_{CEO}	60	V
Emitter-Base Voltage	V_{EBO}	7	V
Collector-Emitter Voltage	V_{CEV}	70	V
Collector Current	I_C	15	A
Collector Peak Current(1)	I_{CM}	15	A
Base Current	I_B	7	A
Base Peak Current(1)	I_{BM}	15	A
Total Dissipation at Ta=25°C	P_D	115	W
Max. Operating Junction Temperature	T_J	+200	°C
Storage Temperature	T_{STG}	-65 ~ 200	°C

Note Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

■ ELECTRICAL CHARACTERISTICS (Ta=25°C, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS						
Collector-Emitter Sustaining Voltage	$V_{CEO(SUS)}$	I_C=200mA, I_B=0V	60			V
Collector-Emitter Sustaining Voltage	$V_{CER(SUS)}$	I_C=0.2 A, R_{BE}=100Ω	70			V
Collector Cut-off Current	I_{CEO}	V_{CE}=30V,I_B=0			0.7	mA
Collector Cut-off Current	I_{CEX}	V_{CE}=100V, $V_{BE(OFF)}$=1.5V V_{CE}=100V, $V_{BE(OFF)}$=1.5V, Ta=150°C			1.0 5.0	mA
Emitter Cut-off Current	I_{EBO}	V_{BE}=7V, I_C=0			5.0	mA
ON CHARACTERISTICS						
DC Current Gain(Note)	h_{FE}	I_C=4A,V_{CE}=4V, I_C=10A,V_{CE}=4V	20 5		70	
Collector-Emitter Saturation Voltage	$V_{CE(SAT)}$	I_C=4A, I_B=400mA I_C=10A, I_B=3.3A			1.1 3.0	V
Base-Emitter On Voltage	$V_{BE(ON)}$	I_C=4A, V_{CE}=4V			1.5	V
SECOND BREAKDOWN						
Second Breakdown Collector with Base Forward Biased	Is/b	V_{CE}=60V, T=1.0s, Non-repetitive	2.87			A
DYNAMIC CHARACTERISTICS						
Current Gain-Bandwidth Product	f_T	I_C=0.5A, V_{CE}=10V, f=1MHz	2.5			MHz
Small-Signal Current Gain	h_{FE}	I_C=1A, V_{CE}=4V, f=1kHz	15		120	
Small-Signal Current Gain Cut-off Frequency	fh_{FE}	I_C=1A, V_{CE}=4V, f=1kHz	10			kHz

Note(1):Pulse Test: PW≦300μs, Duty Cycle≦2%